Selection of Results - Reviewers Only

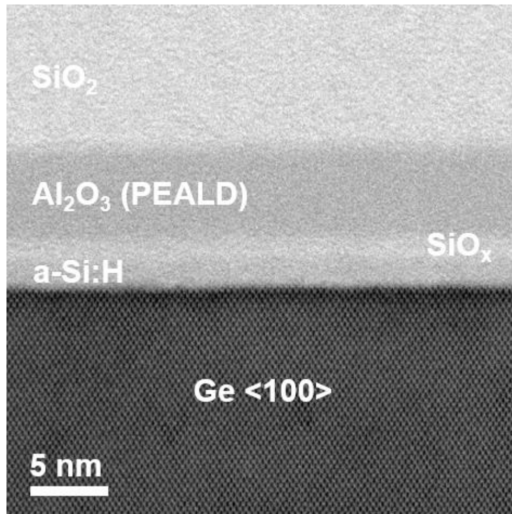

Fig. 1 Cross-sectional bright-field scanning transmission electron microscopy image of a-Si:H/Al_2O_3 stacks on n-type <100> germanium.

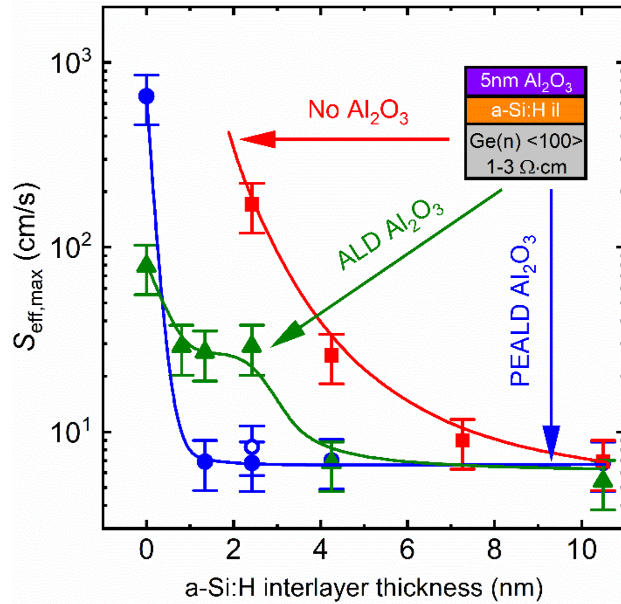

Fig. 2 The maximum effective surface recombination velocity $S_{eff,max}$ measured on Ge (~2 Ω·cm n-type, <100>) as a function of a-Si:H interlayer thickness. Data is presented for a-Si:H without additional capping layer (red), with 50 cycles Al_2O_3 capping layer by thermal ALD (green), and with 50 cycles nm Al_2O_3 capping layer by plasma-enhanced ALD (blue).

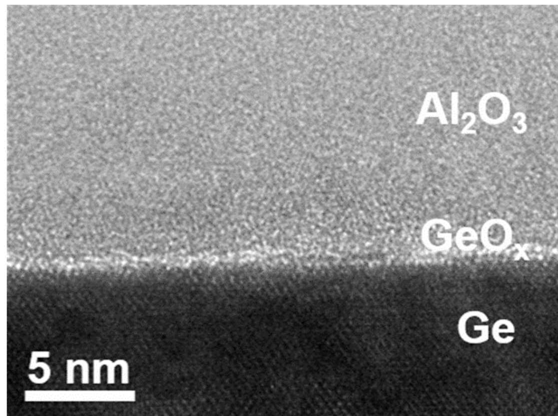

Fig. 3 Cross-sectional bright-field scanning transmission electron microscopy image of plasma-enhance ALD Al_2O_3 on p-type <100> germanium.

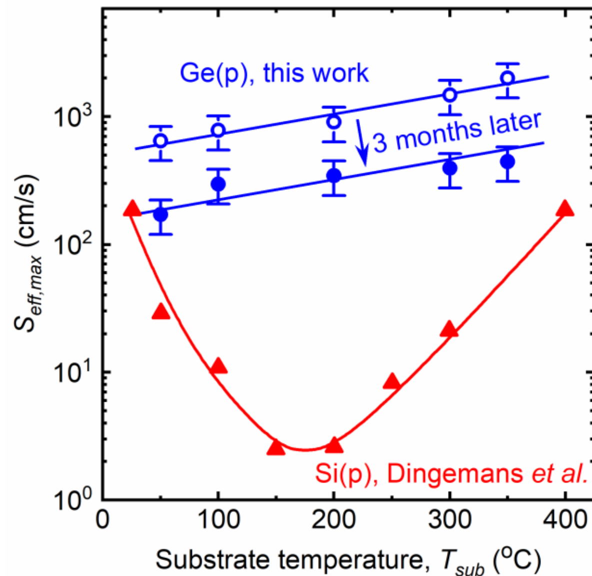

Fig. 4 The effective surface recombination velocity $S_{eff,max}$ as a function of the substrate temperature used during the deposition of Al_2O_3 films on Ge and Si.